IN THE CLAIMS:

1-4. (Canceled)

5. (Previously presented) The method of making a bottom-gate thin-film transistor according to Claim 6, wherein the precursor layer comprises an amorphous silicon film and the active layer comprises a polysilicon film.

6. (Previously presented) The method of making a bottom-gate thin-film transistor according to Claim 9, wherein, in the laminate forming step, the first layer is a precursor layer for an active layer and is formed on the gate insulating film, the precursor layer is crystallized to form an active layer, and then the protective insulating film is formed on the active layer.

7. (Previously presented) The method of making a bottom-gate thin-film transistor according to Claim 9, wherein, in the laminate forming step, the first layer is a precursor layer for an active layer and is formed on the gate insulating film, the protective insulating film is continuously formed on the precursor layer, and then the precursor layer is crystallized to form the active layer.

8. (Canceled)

9. (Previously presented) A method of making a bottom-gate thin-film transistor comprising:

forming a gate electrode on a transparent substrate;

forming a gate insulating film on the gate electrode, the gate insulating film comprising a silicon oxide film formed on a silicon nitride film;

forming a laminate on said gate insulating film, comprising:

forming a first layer, and

forming a protective insulating film having a thickness of about 100 nm or less directly on and in physical contact with said first layer without using an etching process;

implanting a dopant when forming one of an LDD region and a source-drain region of the first layer through the protective insulating film without etching said protective insulating film;

recovering defects formed in the protective insulating film by applying a temperature of about 600 degrees Centigrade subsequent to the dopant implanting step;

activating the implanted dopant; and

forming an interlayer insulating film on the protective insulating film.

10. (Canceled)

11. (Currently amended) A method of fabricating a liquid crystal display device comprising:

making a bottom-gate thin-film transistor by a method according to any one of Claims 5 to 7 and 9;

forming an interlayer insulating film directly on and in physical contact with the protective insulating film of the bottom-gate thin-film transistor, forming a planarizing layer directly on and in physical contact with the interlayer insulating film, forming a transparent electrode directly on and in physical contact with the planarizing layer, and forming an alignment layer directly on and in physical contact with [[a]] the transparent electrode to comprise a TFT substrate; and

interposing a liquid crystal between the TFT substrate and a counter substrate provided with a counter electrode.

12. (Canceled)

13. (Currently amended) A method of fabricating an organic EL device comprising:

making a bottom-gate thin-film transistor by a method according to any one of Claims 5 to 7 and 9;

forming an interlayer insulating film on a protective insulating film of the bottom-gate thin-film transistor; and

forming an organic EL element driven by the bottom-gate thin-film transistor on the interlayer insulating film, the EL element including a luminescent layer sandwiched between a first pair of layers comprising an anode layer and a hole-transporting layer and a second pair of layers comprising an electron-transporting layer and a cathode layer.

14. (Canceled)

15. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the forming of the organic EL element comprises forming the cathode layer, forming the electron-transporting layer, forming the luminescent layer, forming the hole-transporting layer, and forming the anode layer, in this order.

16. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the forming of the organic EL element comprises forming the anode layer, forming the hole-transporting layer, forming the luminescent layer, forming the electron-transporting layer, and forming the cathode layer, in this order.

17. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the cathode layer is composed of a magnesium-indium alloy or an aluminum-lithium alloy.

18. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the electron-transporting layer is composed of a 10-benzo[h]quinolinol-beryllium complex.

19. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the luminescent layer is composed of an 8-quinolinol-aluminum complex containing a quinacridone derivative.

20. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the hole-transporting layer is composed of TPD (4,4',4"-tris-(methylphenylphenylamino)triphenylamine), MTDATA (4,4'-bis(3-methylphenylphenylamino)biphynyl), or α-NPD (α-naphtylphenyldiamine).

21. (Previously presented) A method of fabricating an organic EL device according to Claim 13, wherein the anode layer is composed of platinum, rhodium, or palladium.

22. (Previously presented) The method of making a bottom-gate thin-film transistor according to Claim 7, wherein the precursor layer comprises an amorphous silicon film and the active layer comprises a polysilicon film.